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Data Sheet

September 2013

N-Channel Power MOSFET 50V, 16A, 47 $m\Omega$

The RFD16N05 and RFD16N05SM N-channel power MOSFETs are manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers, and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA09771.

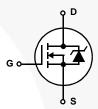
Ordering Information

PART NUMBER	PACKAGE	BRAND		
RFD16N05SM9A	TO-252AA	D16N05		

Features

- 16A, 50V
- $r_{DS(ON)} = 0.047\Omega$
- Temperature Compensating PSPICE[®] Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- 175°C Operating Temperature
- · Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging

JEDEC TO-252AA



RFD16N05SM

Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

	RFD16N05SM9A	UNITS
Drain to Source Voltage (Note 1)	50	V
Drain to Gate Voltage (Note 1)V _{DGR}	50	V
Continuous Drain Current	16	Α
Pulsed Drain Current (Note 3)	Refer to Peak Current Curve	
Gate to Source Voltage	±20	V
Pulsed Avalanche RatingE _{AS}	Refer to Figure 5	
Power Dissipation	72	W
Derate above 25°C	0.48	W/oC
Operating and Storage Temperature	-55 to 175	°C
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	300	οС
Package Body for 10s, See Techbrief 334	260	οС

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}C$ to $150^{\circ}C$.

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST	CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	$I_D = 250\mu A, V_{GS} = 0V \text{ (Figure 11)}$		50	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$		2	-	4	V
Zero Gate Voltage Drain Current	I _{DSS}	I _{DSS} V _{DS} = Rated BV _{DSS} , V _{GS} = 0V		-	-	1	μΑ
$V_{DS} = 0.8 \text{ x Rated BV}_{DSS}, V_{GS} = 0V,$ $T_{C} = 150^{\circ}C$		BV_{DSS} , $V_{GS} = 0V$,	-	-	25	μА	
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V		-	-	±100	nA
Drain to Source On Resistance (Note 2)	r _{DS(ON)}	I _D = 16A, V _{GS} = 10\	/ (Figure 9)	-	-	0.047	Ω
Turn-On Time	t(ON)	V_{DD} = 25V, I_{D} = 8A, R_{L} = 3.125 Ω , V_{GS} = 10V, R_{GS} = 25 Ω (Figure 13)		-	-	65	ns
Turn-On Delay Time	t _d (ON)			-	14	-	ns
Rise Time	t _r			-	30	-	ns
Turn-Off Delay Time	t _d (OFF)			-	55	-	ns
Fall Time	t _f			-	30	-	ns
Turn-Off Time	t(OFF)			-	-	125	ns
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 20V	$V_{DD} = 40V, I_{D} \approx 16A,$	-	-	80	nC
Gate Charge at 10V	Q _{g(10)}	V _{GS} = 0V to 10V	$R_L = 2.5\Omega$ $I_{g(REF)} = 0.8\text{mA}$	-	-	45	nC
Threshold Gate Charge	Q _(TH)	V _{GS} = 0V to 2V	(Figure 13)	-	-	2.2	nC
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz (Figure 12)		-	900	-	pF
Output Capacitance	C _{OSS}			-	325	-	pF
Reverse Transfer Capacitance	C _{RSS}			- /	100	-	pF
Thermal Resistance Junction to Case	$R_{\theta JC}$			-	- //	2.083	oC/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-251 and TO-252		-	-	100	oC/W

Source to Drain Diode Specifications

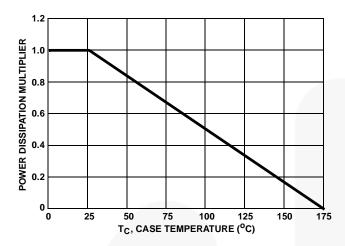
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	I _{SD} = 16A	-	-	1.5	V
Diode Reverse Recovery Time	t _{rr}	$I_{SD} = 16A$, $dI_{SD}/dt = 100A/\mu s$	-	-	125	ns

NOTES:

- 2. Pulse test: pulse width \leq 250 μ s, duty cycle \leq %.
- 3. Repetitive rating: pulse width limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3) and Peak Current Capability Curve (Figure 5).

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Typical Performance Curves Unless Otherwise Specified





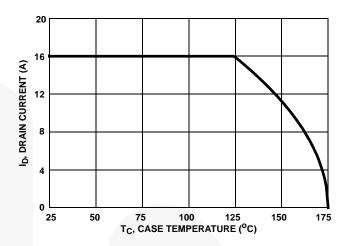


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

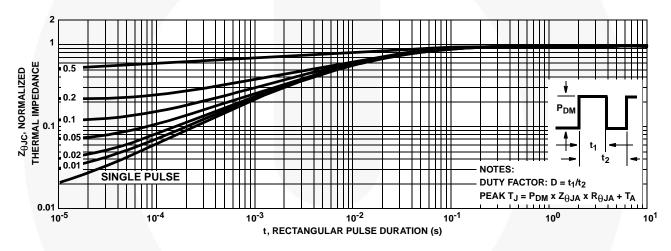


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

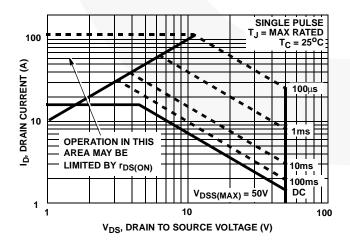


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

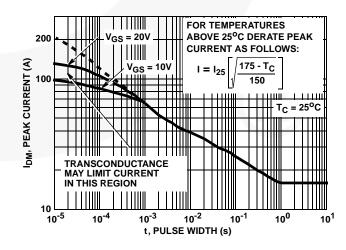
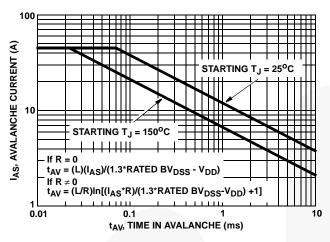


FIGURE 5. PEAK CURRENT CAPABILITY

Typical Performance Curves Unless Otherwise Specified (Continued)



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING

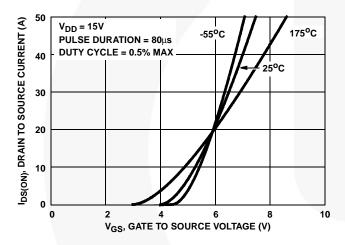


FIGURE 8. TRANSFER CHARACTERISTICS

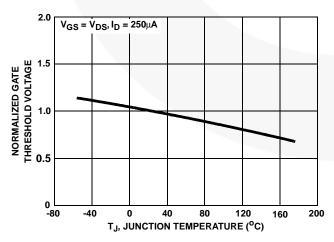


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

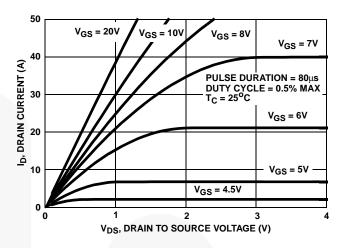


FIGURE 7. SATURATION CHARACTERISTICS

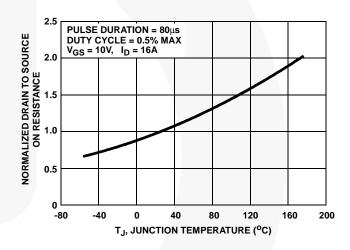


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

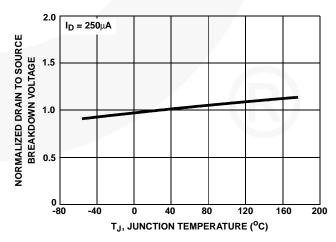


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified (Continued)

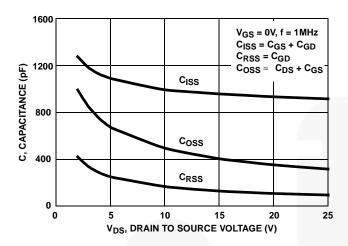
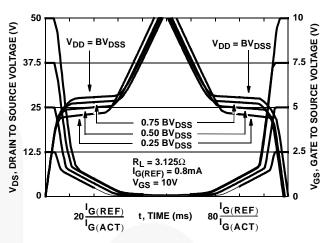


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

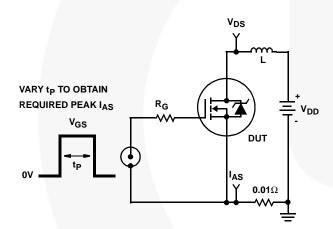


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

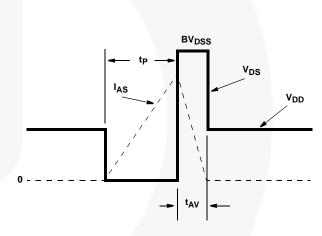


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

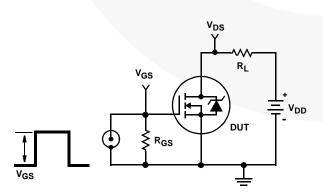


FIGURE 16. SWITCHING TIME TEST CIRCUIT

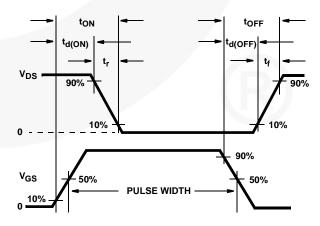


FIGURE 17. RESISTIVE SWITCHING WAVEFORMS

Test Circuits and Waveforms (Continued)

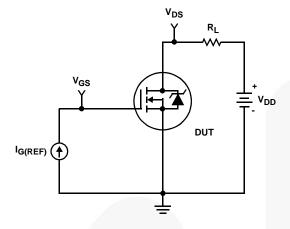


FIGURE 18. GATE CHARGE TEST CIRCUIT

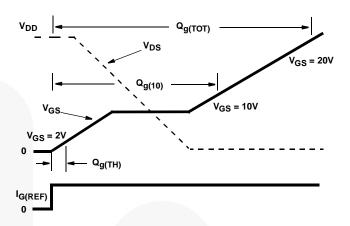


FIGURE 19. GATE CHARGE WAVEFORM

PSPICE Electrical Model

```
.SUBCKT RFD16N05 2 1 3 :
                                 rev 10/31/94
CA 12 8 1.788e-10
CB 15 14 1.875e-10
CIN 6 8 8.33e-10
                                                                   DPLCAP
                                                                                                                 DRAIN
                                                                                                        LDRAIN
DBODY 7 5 DBDMOD
                                                            10
DBREAK 5 11 DBKMOD
DPLCAP 10 5 DPLCAPMOD
                                                                                RSCL1
                                                                                        DBREAK
                                                                               <sub>+</sub> 51
                                                                 RSCL2
EBREAK 11 7 17 18 64.89
                                                                                 ESCL
EDS 14 8 5 8 1
EGS 13 8 6 8 1
                                                                                50
ESG 6 10 6 8 1
                                                                                                         DBODY
                                                                                RDRAIN
                                                                                              11
                                                         ESG (
EVTO 20 6 18 8 1
                                                                           16
                                                                                        EBREAK(
                                                                      VTO
IT 8 17 1
                                                                                 21 |
                                                                                        MOS<sub>2</sub>
                                                       EVTO
                                    GATE
                                         <del>مس</del>_9
                                                   20
                                                        18
LDRAIN 2 5 1e-9
                                                                               MOS1
                                                                           i←
                                                         8
                                       LGATE RGATE
LGATE 1 9 4.56e-9
LSOURCE 3 7 4.13e-9
                                                                RIN >
                                                                         CIN
                                                                                        RSOURCE
                                                                                                       LSOURCE
                                                                                  8
                                                                                                   7
MOS1 16 6 8 8 MOSMOD M = 0.99
                                                                                                           ∽⊸ 3
SOURCE
MOS2 16 21 8 8 MOSMOD M = 0.01
                                                        S1A 6
                                                                 S2A
RBREAK 17 18 RBKMOD 1
                                                                                                  RBREAK
                                                           13
RDRAIN 50 16 RDSMOD 0.4e-3
                                                                                              17
                                                                                                            18
                                                           8
                                                                  13
RGATE 9 20 3.0
RIN 6 8 1e9
                                                                 PS2B
                                                                                                           > RVTO
                                                                  13
RSCL1 5 51 RSCLMOD 1e-6
                                                                                                            19
                                                       CA
                                                                         CB
                                                                                                1
                                                                                                   IT
RSCL2 5 50 1e3
RSOURCE 8 7 RDSMOD 21.5e-3
                                                                                                             VBAT
                                                           EGS
                                                                      EDS
RVTO 18 19 RVTOMOD 1
S1A 6 12 13 8 S1AMOD
S1B 13 12 13 8 S1BMOD
S2A 6 15 14 13 S2AMOD
S2B 13 15 14 13 S2BMOD
VBAT 8 19 DC 1
VTO 21 6 0.82
ESCL 51 50 VALUE = \{(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)*1e6/94,7))\}
.MODEL DBDMOD D (IS = 2.5e-13 RS = 7.1e-3 TRS1 = 3.04e-3 TRS2 = -10e-6 CJO = 1.12e-9 TT = 5.6e-8)
.MODEL DBKMOD D (RS = 2.51e-1 TRS1 = -6.57e-4 TRS2 = 1.66e-6)
.MODEL DPLCAPMOD D (CJO = 6.1e-10 IS = 1e-30 N = 10)
.MODEL MOSMOD NMOS (VTO = 3.96 KP = 16.68 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)
.MODEL RBKMOD RES (TC1 = 1.07e-3 TC2 = -7.19e-7)
.MODEL RDSMOD RES (TC1 = 5.45e-3 TC2 = 1.66e-5)
.MODEL RSCLMOD RES (TC1 = 1.25e-3 TC2 = 17e-6)
.MODEL RVTOMOD RES (TC1 = -5.15e-3 TC2 = -4.83e-6)
.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -5.25 VOFF= -3.25)
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -3.25 VOFF= -5.25)
.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0.56 VOFF= 5.56)
.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 5.56 VOFF= 0.56)
```

.ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; written by William J. Hepp and C. Frank Wheatley.



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